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[0002] This application is related to copending U.S. Patent Application Serial No. 10/039,068 entitled "Method For Fabricating A High Voltage Power MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Rapid Diffusion," filed in the United States Patent and Trademark Office on December 31, 2001.

[0003] This application is related to copending U.S. Patent Application Serial No. 10/038,845 entitled "High Voltage MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching And Ion Implantation," filed in the United States Patent and Trademark Office on December 31, 2001.

[0004] This application is related to copending U.S. Patent Application Serial No. 10/039,241 entitled "High Voltage MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching And Diffusion From Regions of Oppositely Doped Polysilicon" filed in the United States Patent and Trademark Office on December 31, 2001.

STATUS OF CLAIMS

Claims 1-32 are pending.

REMARKS

This is a preliminary amendment before the first Office Action.

Claims 1-32 are pending herein.

The specification is amended to include the previously unknown serial numbers and filing dates of three related co-pending patent applications.

Attached hereto is a marked-up version of the change made to the specification by this preliminary amendment. The attached page is captioned "Version with markings to show changes made".

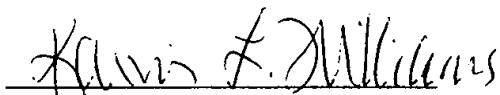
CONCLUSION

Applicant submits Claims 1-32 are in condition for examination, early notification of which is earnestly solicited. Should the Examiner be of the view that an interview would expedite consideration of this Amendment or of the application at large, request is made that the Examiner telephone the Applicant's attorney at (908) 518-7700 in order that any outstanding issues be resolved.

FEES

If there are any fees due and owing in respect to this amendment, the Examiner is authorized to charge such fees to deposit account number 50-1047.

Respectfully submitted,



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Patent
10/039,284

Version with markings to show changes made

In the specification:

[0002] This application is related to copending U.S. Patent Application Serial No. [REDACTED] [GS 157] 10/039,068 entitled "Method For Fabricating A High Voltage Power MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Rapid Diffusion," filed in the United States Patent and Trademark Office on December 31, 2001.

[0003] This application is related to copending U.S. Patent Application Serial No. [REDACTED] [GS 156] 10/038,845 entitled "High Voltage MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching And Ion Implantation," filed in the United States Patent and Trademark Office on December 31, 2001.

[0004] This application is related to copending U.S. Patent Application Serial No. [REDACTED] [GS 175] 10/039,241 entitled "High Voltage MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching And Diffusion From Regions of Oppositely Doped Polysilicon" filed in the United States Patent and Trademark Office on December 31, 2001.